



제 29회 한국반도체학술대회

The 29th Korean Conference on Semiconductors

2022년 1월 24일(월)~ 26일(수) | 강원도 하이원 그랜드호텔(컨벤션타워)

2022년 1월 25일(화), 10:45-12:30

Room K (다이아몬드 I, 6층)

F. Silicon and Group-IV Devices and Integration Technology 분과

[TK2-F] 2D Device Technology

좌장: 김경록 교수(UNIST), 이용규 마스터(삼성전자)

<p>TK2-F-1 10:45-11:15</p>	<p>2D Materials based Atomic Memory and RF Switches Myungsoo Kim <i>Department of Electrical Engineering, UNIST</i></p>
<p>TK2-F-2 11:15-11:30</p>	<p>MoS₂ Thin-Film Transistor with the Gate Stack of Metal-Ferroelectric(Hf_{0.5}Zr_{0.5}O)-Insulator(Al₂O₃) Gisu Youm and Changhwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i></p>
<p>TK2-F-3 11:30-11:45</p>	<p>Effective Work-function Increase Observed in Al/SiO₂/Si Junction with Graphene Interlayer at Al/SiO₂ Interface Wonho Song¹, Jung-Yong Lee², Junhyung Kim¹, Jinyoung Park¹, Eunseok Hyun¹, and Kibog Park^{1,3} <i>¹Department of Physics, UNIST, ²SKKU Quantum Information Research Support Center, Sungkyunkwan University, ³Department of Electrical Engineering, UNIST</i></p>
<p>TK2-F-4 11:45-12:00</p>	<p>Experimental Study of the Impact of Hf_{0.5}Zr_{0.5}O₂ Film Deposition Temperature on Endurance Characteristics Hyeonjung Park, and Changhwan Shin <i>Department of Electrical and Computer Engineering, Sungkyunkwan University</i></p>
<p>TK2-F-5 12:00-12:15</p>	<p>Highly Reliable Electrical Extraction of Density of Grain Boundary States from the Ultrathin Poly-Si MOSFET Channel Inyoung Lee¹, Kyung Song², Seungmin Lee³, Il Hwan Cho¹, and Seongjae Cho³ <i>¹Department of Electronic Engineering, Myongji University, ²Materials Modeling and Characterization Department, KIMS, ³Department of Electronic Engineering, Gachon University</i></p>
<p>TK2-F-6 12:15-12:30</p>	<p>Impact of Plasma Power on Slow Trap Density in Al₂O₃/GeO_x/Ge Structure 이진우, 한승민, 안대환, 한재훈 <i>KIST</i></p>